

	Hits	Search Text	DBs	Time Stamp
1	1580	438/151.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/03/22 15:07
2	2141	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/03/22 15:07
3	381	438/157.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/03/22 15:07
4	392	438/163.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2007/03/22 15:08
5	1	(TEG and TFT).clm.	US-PGPUB	2007/03/22 15:09
6	1885	(TFT).clm.	US-PGPUB	2007/03/22 15:09
7	110	(TFT and gate with (first second) near2 conduct\$3).clm.	US-PGPUB	2007/03/22 15:10
8	1	(TFT and gate with (first second) near2 conduct\$3 and resistance with (test\$3 measur\$3)).clm.	US-PGPUB	2007/03/22 15:11
9	9	(TFT and gate with (first second) near2 conduct\$3 and resistance).clm.	US-PGPUB	2007/03/22 15:11
10	1	(TFT and gate with (first second) near2 conduct\$3 and resistance with (impur\$3 dop\$3)).clm.	US-PGPUB	2007/03/22 15:12
11	1	(TFT and gate with (first second) near2 conduct\$3 and (test\$3 measur\$3) with (impur\$3 dop\$3)).clm.	US-PGPUB	2007/03/22 15:13
12	34	(TFT and gate with (first second) near2 conduct\$3 with semiconductor).clm.	US-PGPUB	2007/03/22 15:13

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13	24	(TFT and gate with (first second) near2 conduct\$3 with etch\$3 and semiconductor).clm.	US-PGPUB	2007/03/22 15:14
14	11	(TFT and gate with (first second) near2 conduct\$3 with etch\$3 and semiconductor with (first second) near2 conduct\$3).clm.	US-PGPUB	2007/03/22 15:14